

# DATA SHEET

## **TDA1517ATW**

**8 W BTL or 2 × 4 W SE power  
amplifier**

Product specification  
Supersedes data of 2001 Feb 14  
File under Integrated Circuits, IC01

2001 Apr 17

## 8 W BTL or 2 × 4 W SE power amplifier

## TDA1517ATW

## FEATURES

- Requires very few external components
- Flexibility in use: mono Bridge-Tied Load (BTL) and stereo Single-Ended (SE); it should be noted that in stereo applications the outputs of both amplifiers are in opposite phase
- High output power
- Low offset voltage at output (important for BTL)
- Fixed gain
- Good ripple rejection
- Mode select switch (operating, mute and standby)
- AC and DC short-circuit safe to ground and  $V_P$
- Electrostatic discharge protection
- Thermal protection
- Reverse polarity safe
- Capable of handling high energy on outputs ( $V_P = 0$  V)
- No switch-on/switch-off plop
- Low thermal resistance.

## GENERAL DESCRIPTION

The TDA1517ATW is an integrated class-AB output amplifier contained in a plastic heatsink thin shrink small outline package (HTSSOP20). The device is primarily developed for multimedia applications.

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_P$	supply voltage		6	12	18	V
$I_{ORM}$	repetitive peak output current		–	–	2.5	A
$I_{q(tot)}$	total quiescent current		–	40	80	mA
$I_{stb}$	standby current		–	0.1	100	$\mu$ A
<b>SE application</b>						
$P_o$	output power	THD = 10%; $R_L = 4 \Omega$	–	4	–	W
SVRR	supply voltage ripple rejection	$R_S = 0 \Omega$	46	–	–	dB
$\alpha_{cs}$	channel separation	$R_S = 10 \text{ k}\Omega$	40	55	–	dB
$V_{n(o)}$	noise output voltage	$R_S = 0 \Omega$	–	50	–	$\mu$ V
$ Z_i $	input impedance		50	–	–	$\text{k}\Omega$
<b>BTL application</b>						
$P_o$	output power	THD = 10%; $R_L = 8 \Omega$	–	8	–	W
SVRR	supply voltage ripple rejection	$R_S = 0 \Omega$	50	–	–	dB
$ \Delta V_{OO} $	output offset voltage		–	–	150	mV
$V_{n(o)(offset)}$	noise output offset voltage	$R_S = 0 \Omega$	–	70	–	$\mu$ V
$ Z_i $	input impedance		25	–	–	$\text{k}\Omega$

## ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
TDA1517ATW	HTSSOP20	plastic, heatsink thin shrink small outline package; 20 leads; body width 4.4 mm	SOT527-1

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BLOCK DIAGRAM

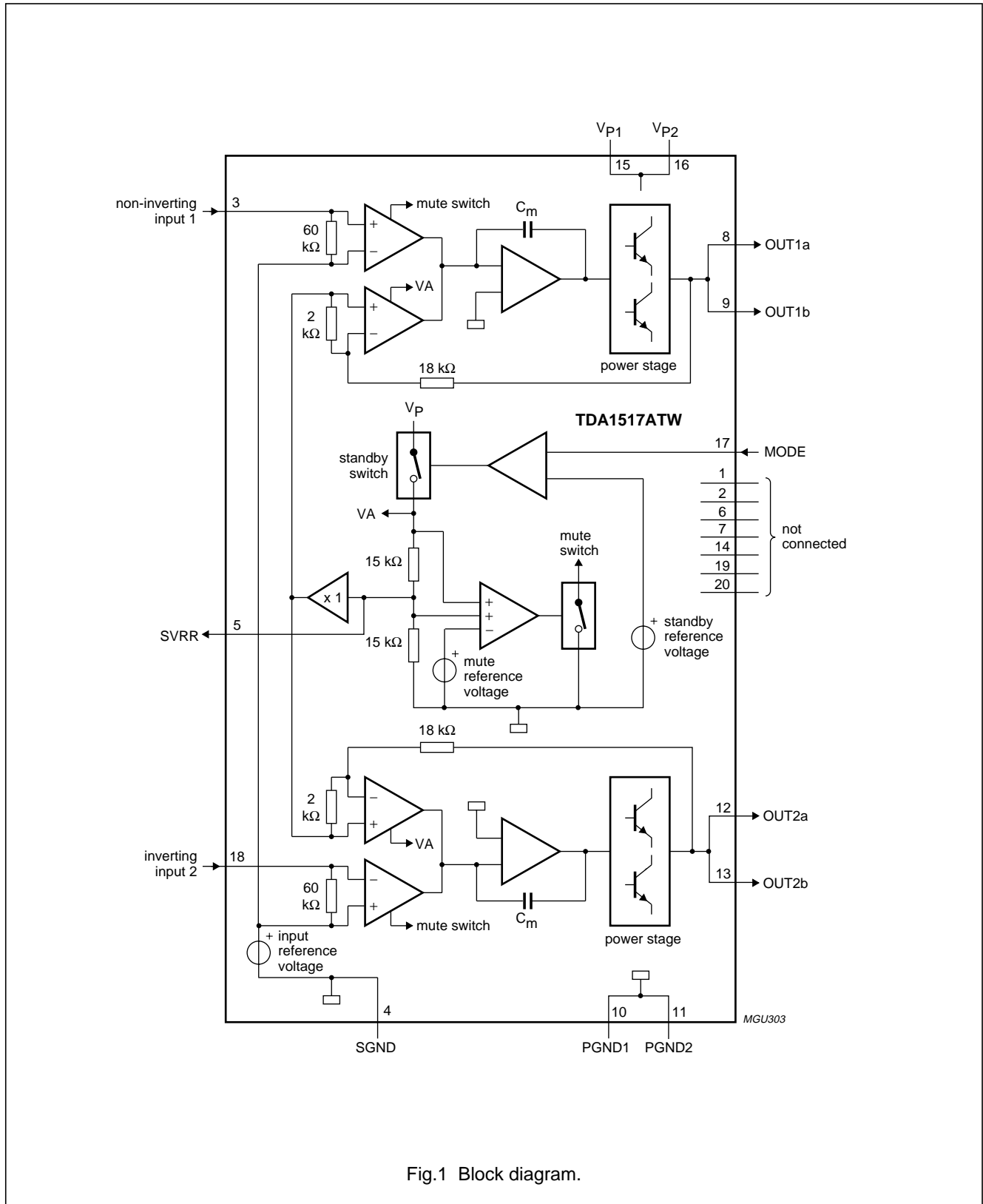


Fig.1 Block diagram.

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## PINNING

SYMBOL	PIN	DESCRIPTION
n.c.	1	not connected
n.c.	2	not connected
IN1+	3	non-inverting input 1
SGND	4	signal ground
SVRR	5	supply voltage ripple rejection
n.c.	6	not connected
n.c.	7	not connected
OUT1a	8	output 1a
OUT1b	9	output 1b
PGND1	10	power ground 1
PGND2	11	power ground 2
OUT2a	12	output 2a
OUT2b	13	output 2b
n.c.	14	not connected
V <sub>P1</sub>	15	supply voltage 1
V <sub>P2</sub>	16	supply voltage 2
MODE	17	mode select switch
IN2-	18	inverting input 2
n.c.	19	not connected
n.c.	20	not connected

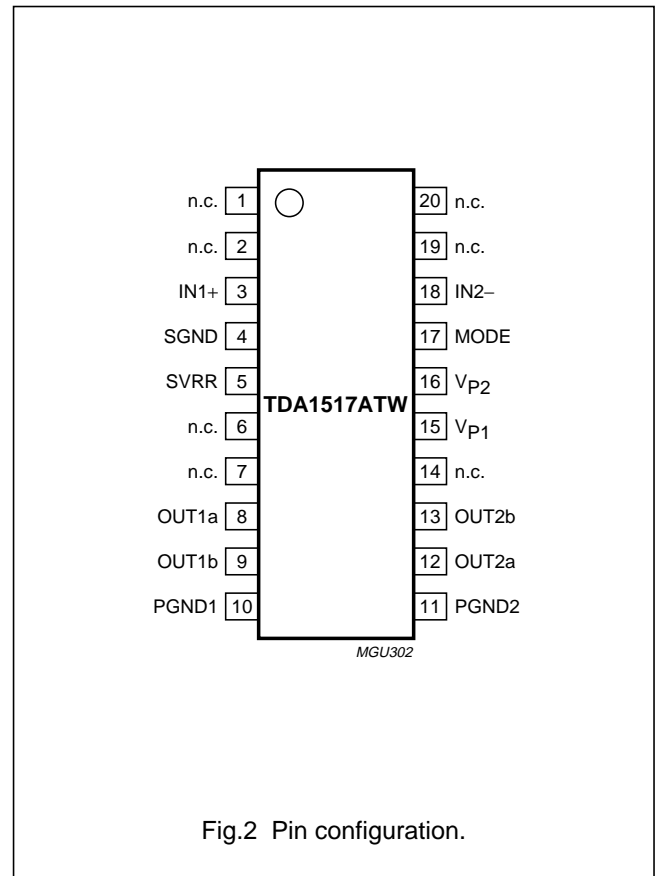


Fig.2 Pin configuration.

## FUNCTIONAL DESCRIPTION

The TDA1517ATW contains two identical amplifiers with differential input stages. This device can be used for Bridge-Tied Load (BTL) or Single-Ended (SE) applications. The gain of each amplifier is fixed at 20 dB. A special feature of this device is the mode select switch. Since this pin has a very low input current (<40  $\mu$ A), a low cost supply switch can be used. With this switch the TDA1517ATW can be switched into three modes:

- Standby: low supply current
- Mute: input signal suppressed
- Operating: normal on condition.

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT.
$V_P$	supply voltage		–	18	V
$V_{PSC}$	AC and DC short-circuit-safe voltage		–	18	V
$V_{rp}$	reverse polarity voltage		–	6	V
$ERG_o$	energy handling capability at outputs	$V_P = 0$ V	–	200	mJ
$I_{OSM}$	non-repetitive peak output current		–	4	A
$I_{ORM}$	repetitive peak output current		–	2.5	A
$P_{tot}$	total power dissipation		–	5	W
$T_{vj}$	virtual junction temperature		–	150	°C
$T_{stg}$	storage temperature		–55	+150	°C
$T_{amb}$	ambient temperature		–40	+85	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
tb <sub>f</sub>			–	–

**DC CHARACTERISTICS** $V_P = 12$  V;  $T_{amb} = 25$  °C; measured in Fig.3; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Supply</b>						
$V_P$	supply voltage	note 1	6.0	12	18	V
$I_q$	quiescent current	$R_L = \infty$	–	40	80	mA
<b>Operating condition</b>						
$V_{MODE(oper)}$	mode switch voltage level		8.5	–	$V_P$	V
$I_{MODE(oper)}$	mode switch current	$V_{MODE} = 12$ V	–	15	40	μA
$V_O$	DC output voltage		–	5.7	–	V
$ \Delta V_{OO} $	DC output offset voltage		–	–	150	mV
<b>Mute condition</b>						
$V_{MODE(mute)}$	mode switch voltage level		3.3	–	6.4	V
$V_O$	DC output voltage		–	5.7	–	V
$ \Delta V_{OO} $	DC output offset voltage		–	–	150	mV
<b>Standby condition</b>						
$V_{MODE(stb)}$	mode switch voltage level		0	–	2	V
$I_{stb}$	standby current		–	0.1	100	μA

**Note**1. The circuit is DC adjusted at  $V_P = 6$  to 18 V and AC operating at  $V_P = 8.5$  to 18 V.

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**AC CHARACTERISTICS**

$V_P = 12\text{ V}$ ;  $f = 1\text{ kHz}$ ;  $T_{\text{amb}} = 25\text{ °C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>SE application; note 1</b>						
$P_o$	output power	note 2				
		THD = 1%	2.5	3.3	–	W
		THD = 10%	3	4	–	W
THD	total harmonic distortion	$P_o = 1\text{ W}$	–	0.1	–	%
$f_{ro(L)}$	low frequency roll-off	–1 dB; note 3	–	25	–	Hz
$f_{ro(H)}$	high frequency roll off	–1 dB	20	–	–	kHz
$G_V$	voltage gain		19	20	21	dB
$ \Delta G_V $	channel balance		–	–	1	dB
SVRR	supply voltage ripple rejection	note 4				
		on	46	–	–	dB
		mute	46	–	–	dB
		standby	80	–	–	dB
$ Z_i $	input impedance		50	60	75	k $\Omega$
$V_{n(o)(rms)}$	noise output voltage (RMS value)	note 5				
		on; $R_S = 0\ \Omega$	–	50	–	$\mu\text{V}$
		on; $R_S = 10\ \text{k}\Omega$	–	70	100	$\mu\text{V}$
		mute; note 6	–	50	–	$\mu\text{V}$
$\alpha_{CS}$	channel separation	$R_S = 10\ \text{k}\Omega$	40	55	–	dB
$V_{o(mute)}$	output voltage in mute	note 7	–	–	2	mV
<b>BTL application; note 8</b>						
$P_o$	output power	note 2				
		THD = 1%	5	6.6	–	W
		THD = 10%	6.5	8.0	–	W
THD	total harmonic distortion	$P_o = 1\text{ W}$	–	0.03	–	%
$f_{ro(L)}$	low frequency roll-off	–1 dB; note 3	–	25	–	Hz
$f_{ro(H)}$	high frequency roll off	–1 dB	20	–	–	kHz
$G_V$	voltage gain		25	26	27	dB
SVRR	supply voltage ripple rejection	note 4				
		on	50	–	–	dB
		mute	50	–	–	dB
		standby	80	–	–	dB
$ Z_i $	input impedance		25	30	38	k $\Omega$
$V_{n(o)(rms)}$	noise output voltage (RMS value)	note 5				
		on; $R_S = 0\ \Omega$	–	70	–	$\mu\text{V}$
		on; $R_S = 10\ \text{k}\Omega$	–	100	200	$\mu\text{V}$
		mute; note 6	–	60	–	$\mu\text{V}$
$V_{o(mute)}$	output voltage in mute	note 7	–	–	2	mV

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### Notes to the characteristics

1.  $R_L = 4 \Omega$ , measured in Fig.4.
2. Output power is measured directly at the output pins of the IC.
3. Frequency response externally fixed.
4.  $V_{ripple} = V_{ripple(max)} = 2 \text{ V (p-p)}$ ;  $R_S = 0 \Omega$ .
5. Noise voltage measured in a bandwidth of 20 Hz to 20 kHz.
6. Noise output voltage independent of  $R_S$ .
7.  $V_i = V_{i(max)} = 1 \text{ V (RMS)}$ .
8.  $R_L = 8 \Omega$ , measured in Fig.3.

### APPLICATION INFORMATION

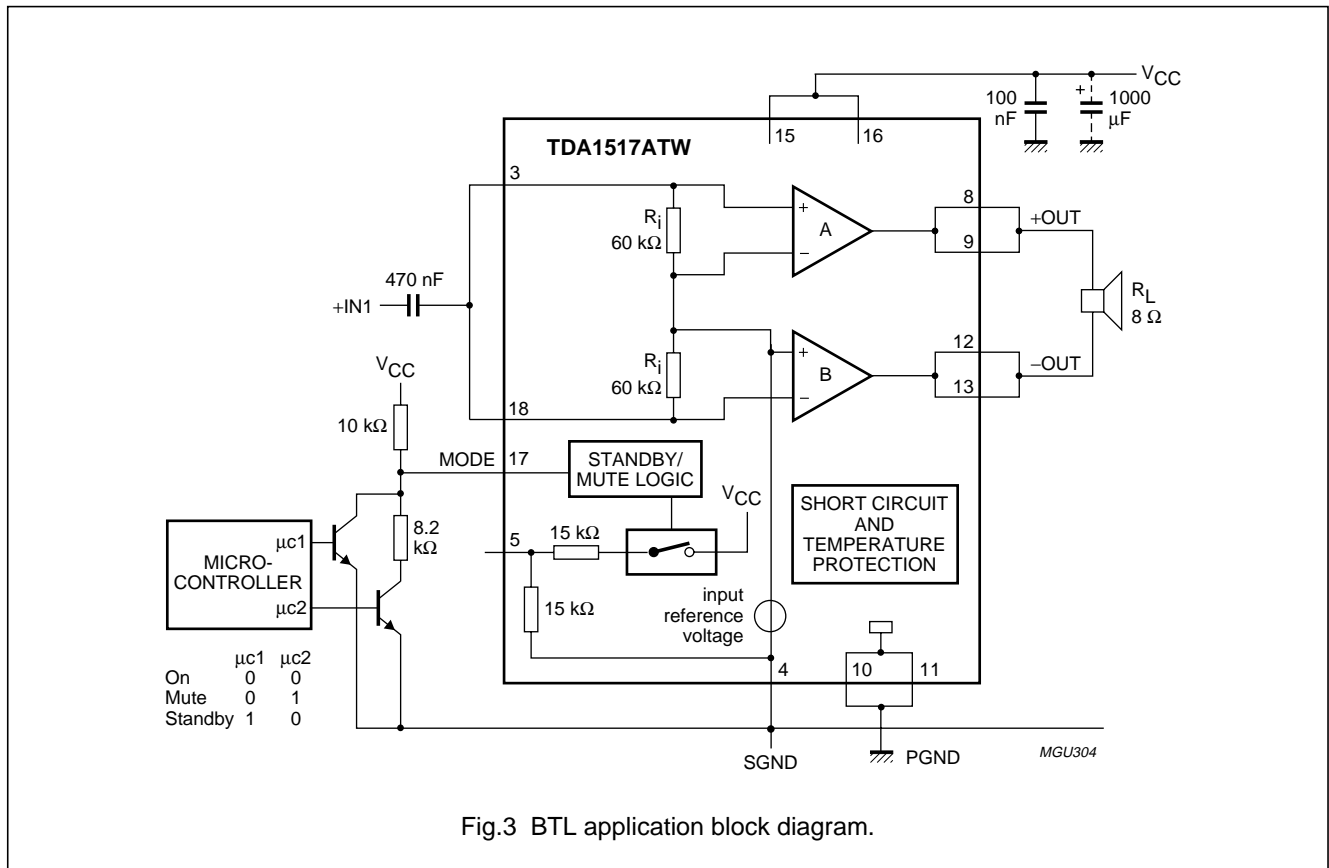


Fig.3 BTL application block diagram.

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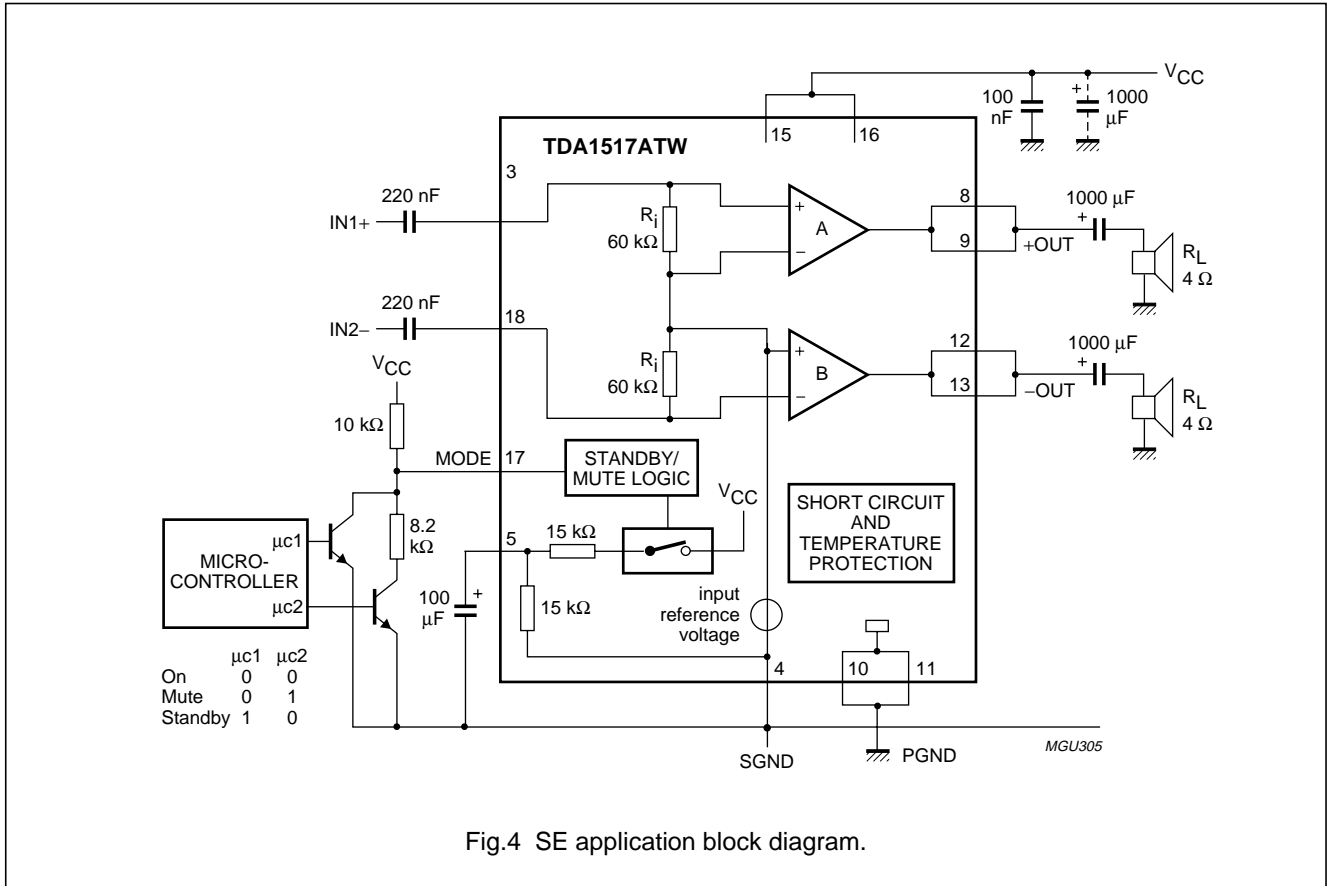


Fig.4 SE application block diagram.

**Test conditions**

T<sub>amb</sub> = 25 °C; unless otherwise specified: V<sub>P</sub> = 12 V, BTL application, f = 1 kHz, R<sub>L</sub> = 8 Ω, fixed gain = 26 dB, audio band-pass: 22 Hz to 22 kHz. In the figures as a function of frequency a band-pass of 10 Hz to 80 kHz was applied.

The BTL application block diagram is shown in Fig.3. The PCB layout [which accommodates both the mono (BTL) and stereo (single-ended) application] is shown in Fig.6.

**Printed-Circuit Board (PCB) layout and grounding**

For high system performance levels certain grounding techniques are imperative. The input reference grounds have to be tied to their respective source grounds and must have separate traces from the power ground traces; this will separate the large (output) signal currents from interfering with the small AC input signals. The small signal ground traces should be located physically as far as possible from the power ground traces. Supply and output traces should be as wide as possible for delivering maximum output power.

Proper supply bypassing is critical for low noise performance and high power supply rejection. The respective capacitor locations should be as close as possible to the device and grounded to the power ground. Decoupling the power supply also prevents unwanted oscillations. For suppressing higher frequency transients (spikes) on the supply line a capacitor with low ESR (typical 0.1 μF) has to be placed as close as possible to the device. For suppressing lower frequency noise and ripple signals, a large electrolytic capacitor (e.g. 1000 μF or greater) must be placed close to the IC.

In single-ended (stereo) application a bypass capacitor connected to pin SVR reduces the noise and ripple on the midrail voltage. For good THD and noise performance a low ESR capacitor is recommended.

**Input configuration**

It should be noted that the DC level of the input pins is approximately 2.1 V; a coupling capacitor is therefore necessary.



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The formula for the cut-off frequency at the input is as

$$\text{follows: } f_{IC} = \frac{1}{2 \times \pi \times R_1 \times C_1}$$

$$\text{thus } f_{IC} = \frac{1}{2 \times \pi \times 30 \times 10^{-3} \times 470 \times 10^{-9}} = 11 \text{ Hz}$$

As can be seen it is not necessary to use high capacitor values for the input; so the delay during switch-on, which is necessary for charging the input capacitors, can be minimized. This results in a good low frequency response and good switch-on behaviour.

In stereo applications (single-ended) coupling capacitors on both input and output are necessary. It should be noted that the outputs of both amplifiers are in opposite phase.

### Built-in protection circuits

The IC contains two types of protection circuits:

- Short-circuits the outputs to ground, the supply to ground and across the load: short-circuit is detected and controlled by a SOAR protection circuit
- Thermal shut-down protection: the junction temperature is measured by a temperature sensor. Thermal foldback is activated at a junction temperature of >150 °C.

### Output power

The output power as a function of supply voltage has been measured on the output pins and at THD = 10%. The maximum output power is limited by the maximum allowable power dissipation and the maximum available output current, 2.5 A repetitive peak current.

### Supply voltage ripple rejection

The SVRR has been measured without an electrolytic capacitor on pin 5 and at a bandwidth of 10 Hz to 80 kHz. The curves for operating and mute condition (respectively) were measured with  $R_{\text{source}} = 0 \Omega$ . Only in single-ended applications is an electrolytic capacitor (e.g. 100  $\mu\text{F}$ ) on pin 5 necessary to improve the SVRR behaviour.

### Headroom

A typical music CD requires at least 12 dB (is factor 15.85) dynamic headroom (compared with the average power output) for passing the loudest portions without distortion. The following calculation can be made for this application at  $V_P = 12 \text{ V}$  and  $R_L = 8 \Omega$ :  $P_o$  at THD = 0.1% is approximately 5 W (see Fig.7).

Average listening level without any distortion yields:

$$P_{\text{ALL}} = \frac{P_{\text{tot}}}{\text{factor}} = \frac{5}{15.85} = 315 \text{ mW}$$

The power dissipation can be derived from Fig.11 for 0 dB and 12 dB headroom.

**Table 1** Power rating

RATING	HEADROOM	POWER DISSIPATION
$P_o = 5 \text{ W}$ (THD = 0.1%)	0 dB	3.5 W
	12 dB	2.0 W

Thus for the average listening level (music power) a power dissipation of 2.0 W can be used for the thermal PCB calculation; see Section "Thermal behaviour (PCB design considerations)".

### Mode pin

For the 3 functional modes: standby, mute and operate, the MODE pin can be driven by a 3-state logic output stage, e.g. a microcontroller with some extra components for DC-level shifting; see Fig.10 for the respective DC levels.

- Standby mode is activated by a low DC level between 0 and 2 V. The power consumption of the IC will be reduced to <0.12 mW.
- Mute mode is activated by a DC level between 3.3 and 6.4 V. The outputs of the amplifier will be muted (no audio output); however the amplifier is DC biased and the DC level of the output pins stays at half the supply voltage. The input coupling capacitors are charged when in mute mode to avoid pop-noise.
- The IC will be in the operating condition when the voltage at pin MODE is between 8.5 V and  $V_{CC}$ .

### Switch-on/switch-off

To avoid audible plops during switch-on and switch-off of the supply voltage, the MODE pin has to be set in standby condition ( $V_{CC}$  level) before the voltage is applied (switch-on) or removed (switch-off). The input and SVRR capacitors are smoothly charged during mute mode.

The turn-on and turn-off time can be influenced by an RC-circuit connected to the MODE pin. Switching the device or the MODE pin rapidly on and off may cause 'click and pop' noise. This can be prevented by proper timing on the MODE pin. Further improvement in the BTL application can be obtained by connecting an electrolytic capacitor (e.g. 100  $\mu\text{F}$ ) between the SVRR pin and signal ground.

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**Thermal behaviour (PCB design considerations)**

The typical thermal resistance [ $R_{th(j-a)}$ ] of the IC in the HTSSOP20 package is 37 K/W if the IC is soldered on a printed-circuit board with double sided 35  $\mu\text{m}$  copper with a minimum area of approximately 30  $\text{cm}^2$ . The actual usable thermal resistance depends strongly on the mounting method of the device on the printed-circuit board, the soldering method and the area and thickness of the copper on the printed-circuit board.

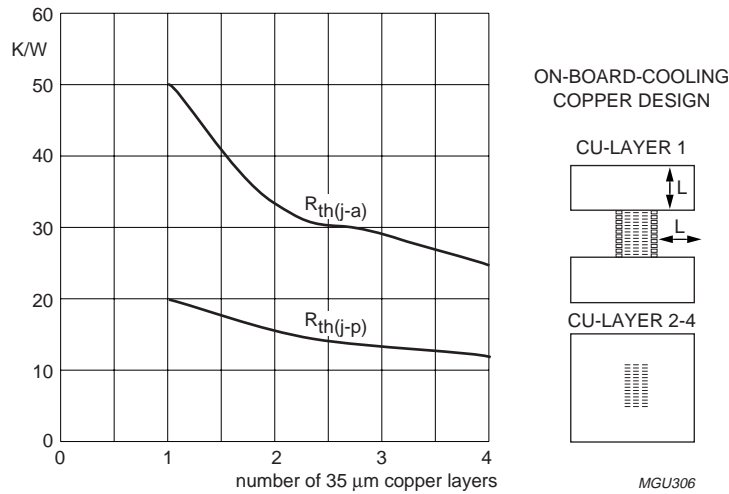
The bottom 'heat-spreader' of the IC has to be soldered efficiently on the 'thermal land' of the copper area of the printed-circuit board using the re-flow solder technique.

A number of thermal vias in the 'thermal land' provide a thermal path to the opposite copper site of the printed-circuit board. The size of the surface layers should be as large as needed to dissipate the heat.

The thermal vias (0.3 mm  $\varnothing$ ) in the 'thermal land' should not use web construction techniques, because those will have high thermal resistance; continuous connection completely around the via-hole is recommended.

For a maximum ambient temperature of 60  $^{\circ}\text{C}$  the following calculation can be made: for the application at  $V_P = 12\text{ V}$  and  $R_L = 8\ \Omega$  the (ALL-) music power dissipation approximately 2.0 W;  
 $T_{j(max)} = T_{amb} + P \times R_{th(j-a)} = 60\ ^{\circ}\text{C} + 2.0 \times 37 = 134\ ^{\circ}\text{C}$ .

Note: the above calculation holds for application at 'average listening level' music output signals. Applying (or testing) with sine wave signals will produce approximately twice the music power dissipation; at worst case condition this can activate the maximum temperature protection.

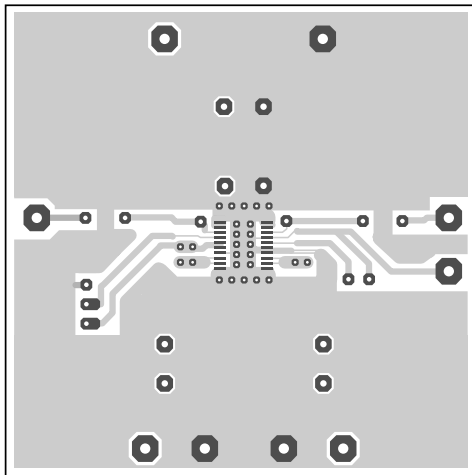


$R_{th(j-p)}$  curve is given for practical calculation purpose.  
 L = 30 mm plus vias

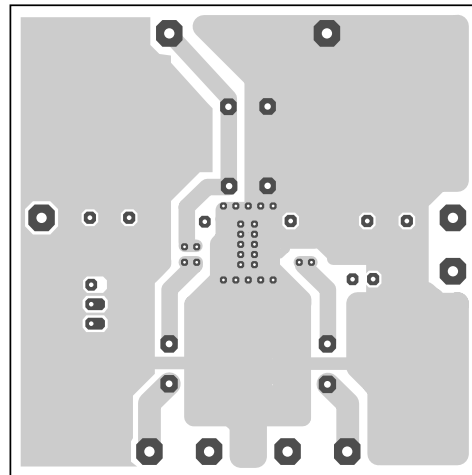
Fig.5 Thermal resistance of the HTSSOP20 mounted on printed-circuit board.

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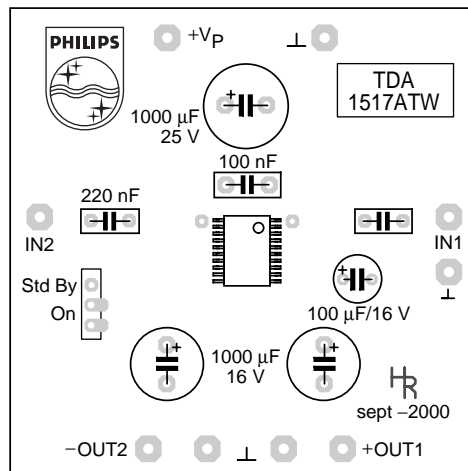
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top view  
bottom copper layout



top view  
top copper layout



MGU312

top view  
component layout

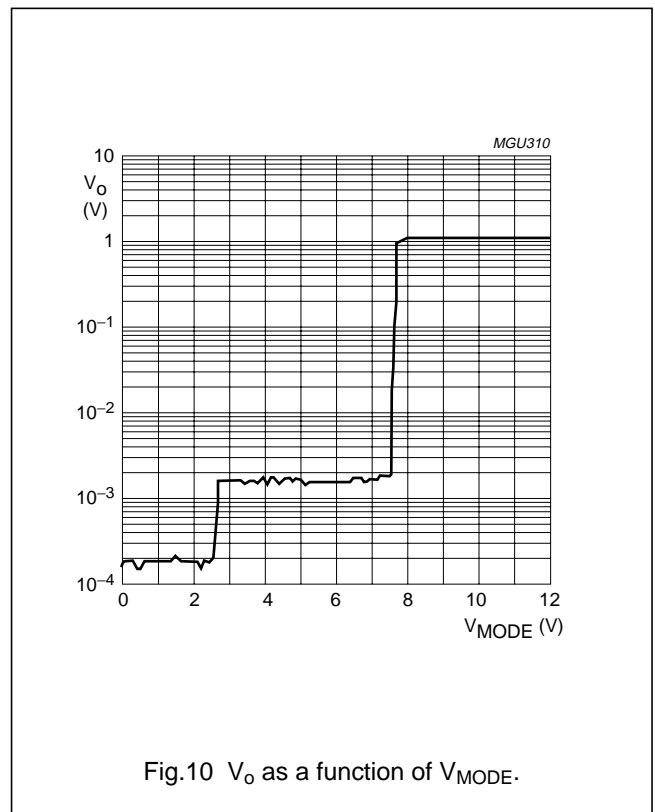
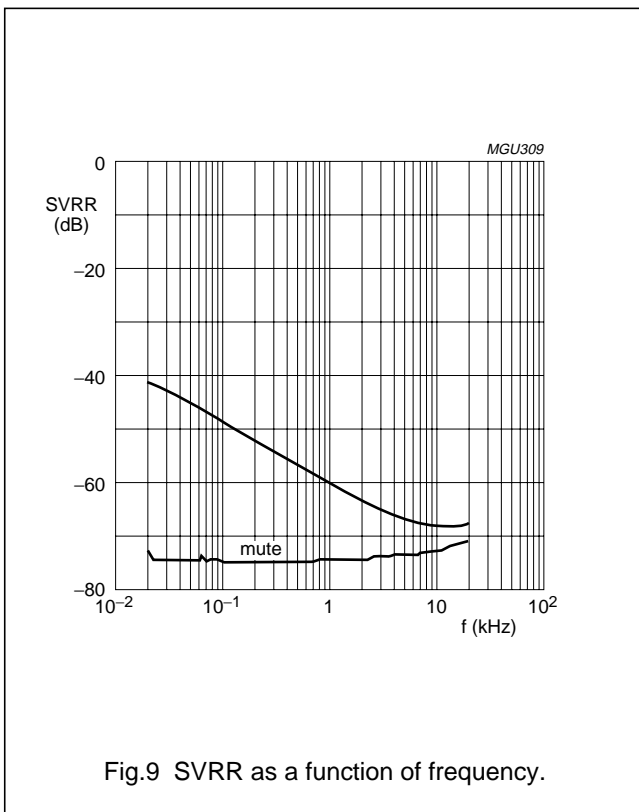
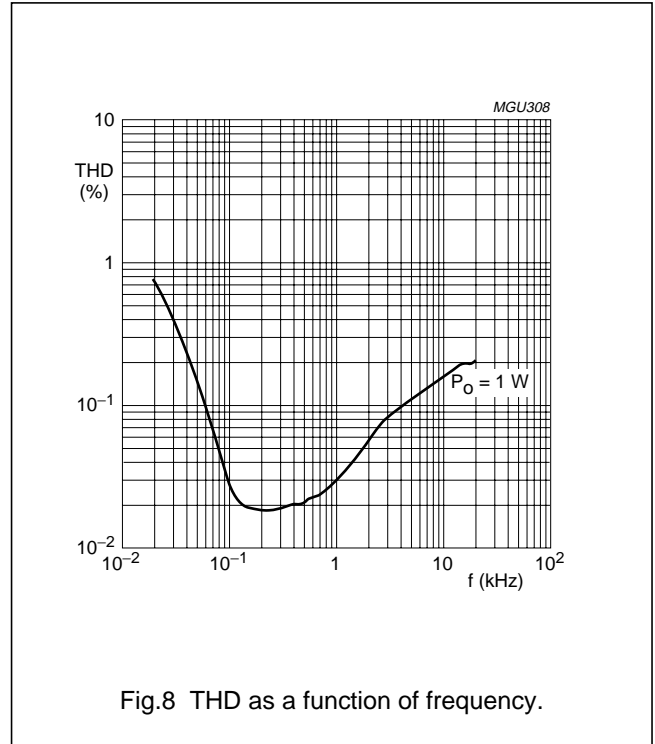
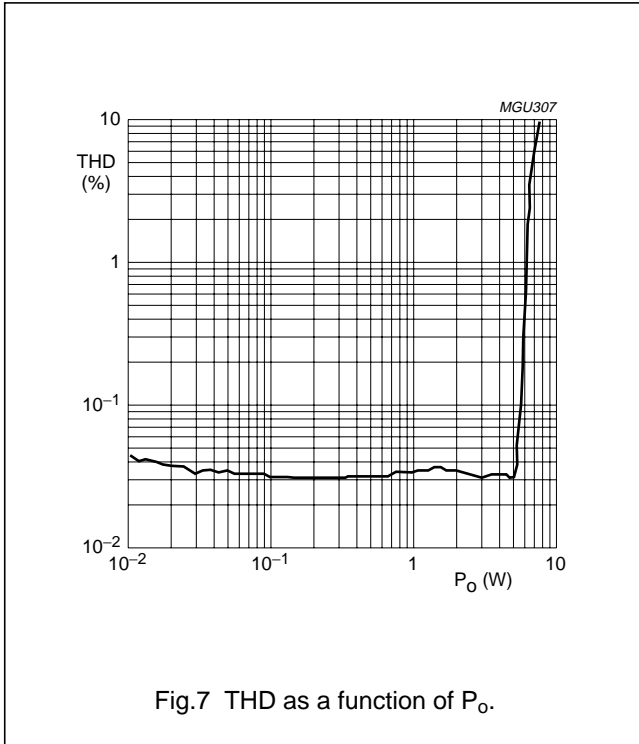
For BTL applications the two 1000  $\mu\text{F}$ /16 V capacitors must be replaced by 0  $\Omega$  jumpers.

Fig.6 Printed-circuit board layout for BTL and SE application.

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Typical performance characteristics for BTL application at  $V_P = 12\text{ V}$  and  $R_L = 8\ \Omega$



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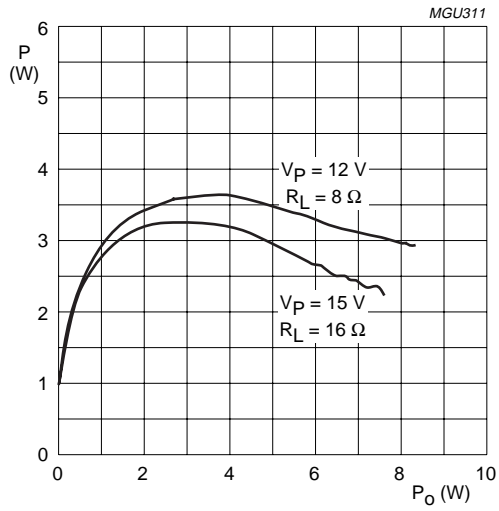


Fig.11 Power dissipation as a function of  $P_o$ .

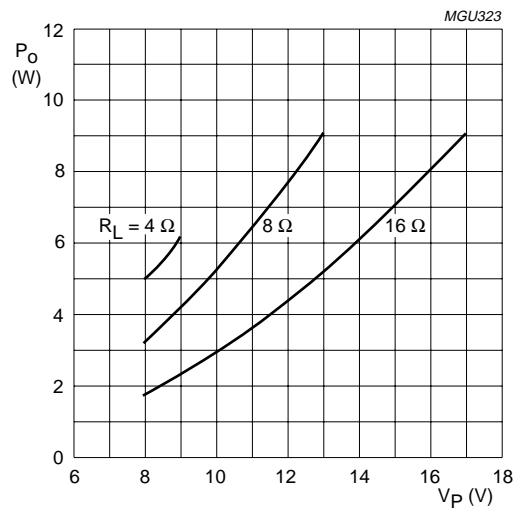


Fig.12  $P_o$  as a function of  $V_p$ .

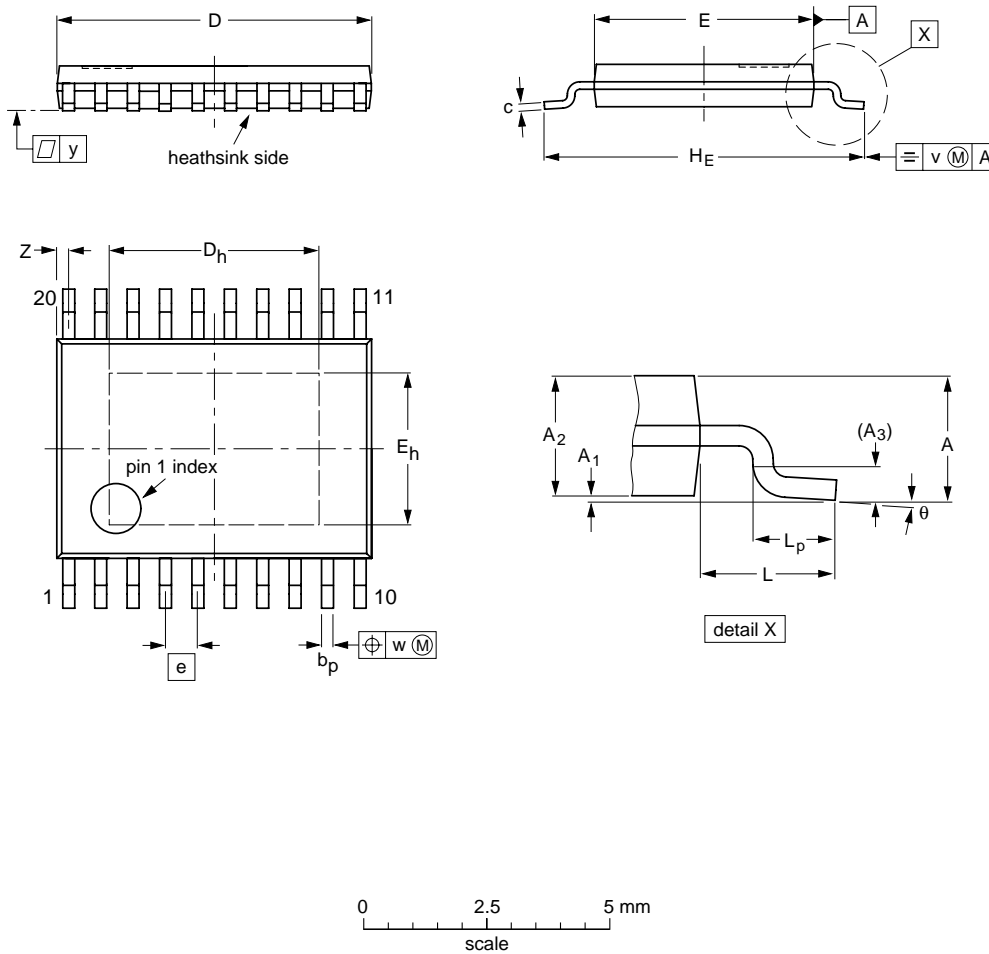
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PACKAGE OUTLINE

HTSSOP20: plastic, heatsink thin shrink small outline package; 20 leads; body width 4.4 mm

SOT527-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	D <sub>h</sub>	E <sup>(2)</sup>	E <sub>h</sub>	e	H <sub>E</sub>	L	L <sub>p</sub>	v	w	y	z <sup>(1)</sup>	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.20 0.09	6.6 6.4	4.3 4.1	4.5 4.3	3.1 2.9	0.65	6.6 6.2	1.0	0.75 0.50	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT527-1						99-11-12-00-07-12

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**SOLDERING****Introduction to soldering surface mount packages**

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

**Reflow soldering**

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

**Wave soldering**

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

**Manual soldering**

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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## Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW <sup>(1)</sup>
BGA, HBGA, LFBGA, SQFP, TFBGA	not suitable	suitable
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, SMS	not suitable <sup>(2)</sup>	suitable
PLCC <sup>(3)</sup> , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended <sup>(3)(4)</sup>	suitable
SSOP, TSSOP, VSO	not recommended <sup>(5)</sup>	suitable

## Notes

1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.



## 8 W BTL or 2 × 4 W SE power amplifier

TDA1517ATW

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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## Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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8 W BTL or 2 × 4 W SE power amplifier

TDA1517ATW

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**NOTES**

8 W BTL or 2 × 4 W SE power amplifier

TDA1517ATW

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**NOTES**

# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 3 Figtree Drive, HOMEBUSH, NSW 2140,  
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

**Belgium:** see The Netherlands

**Brazil:** see South America

**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 68 9211, Fax. +359 2 68 9102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Sydhavnsgade 23, 1780 COPENHAGEN V,  
Tel. +45 33 29 3333, Fax. +45 33 29 3905

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615 800, Fax. +358 9 6158 0920

**France:** 7 - 9 Rue du Mont Valérien, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 4728 6600, Fax. +33 1 4728 6638

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

**Hungary:** Philips Hungary Ltd., H-1119 Budapest, Fehervari ut 84/A,  
Tel: +36 1 382 1700, Fax: +36 1 382 1800

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor,  
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,  
Tel. +91 22 493 8541, Fax. +91 22 493 0966

**Indonesia:** PT Philips Development Corporation, Semiconductors Division,  
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,  
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),  
Tel. +39 039 203 6838, Fax +39 039 203 6800

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,  
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Pakistan:** see Singapore

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Al.Jerozolimskie 195 B, 02-222 WARSAW,  
Tel. +48 22 5710 000, Fax. +48 22 5710 001

**Portugal:** see Spain

**Romania:** see Italy

**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,  
Tel. +7 095 755 6918, Fax. +7 095 755 6919

**Singapore:** Lorong 1, Toa Payoh, SINGAPORE 319762,  
Tel. +65 350 2538, Fax. +65 251 6500

**Slovakia:** see Austria

**Slovenia:** see Italy

**South Africa:** S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,  
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,  
Tel. +27 11 471 5401, Fax. +27 11 471 5398

**South America:** Al. Vicente Pinzon, 173, 6th floor,  
04547-130 SÃO PAULO, SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
Tel. +41 1 488 2741 Fax. +41 1 488 3263

**Taiwan:** Philips Semiconductors, 5F, No. 96, Chien Kuo N. Rd., Sec. 1,  
TAIPEI, Taiwan Tel. +886 2 2134 2451, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
60/14 MOO 11, Bangna Trad Road KM. 3, Bagna, BANGKOK 10260,  
Tel. +66 2 361 7910, Fax. +66 2 398 3447

**Turkey:** Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,  
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

**Uruguay:** see South America

**Vietnam:** see Singapore

**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,  
Tel. +381 11 3341 299, Fax.+381 11 3342 553

**For all other countries apply to:** Philips Semiconductors,  
Marketing Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN,  
The Netherlands, Fax. +31 40 27 24825

**Internet:** <http://www.semiconductors.philips.com>

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